

**Silicon PNP Power Transistors**

**2SA671**

**DESCRIPTION**

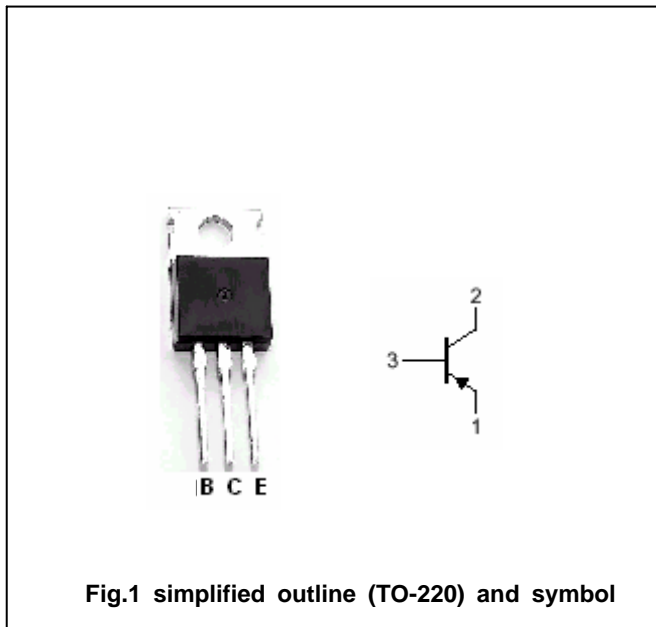
- With TO-220 package
- Complement to type 2SC1061
- Low collector saturation voltage
- Note: type 2SA670 with short pin

**APPLICATIONS**

- Designed for use in low frequency power amplifier applications

**PINNING**

PIN	DESCRIPTION
1	Emitter
2	Collector; connected to mounting base
3	Base



**Absolute maximum ratings(Ta=25 )**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	-50	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	-50	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-4	V
I <sub>C</sub>	Collector current		-3	A
I <sub>CM</sub>	Collector current-peak		-6	A
I <sub>B</sub>	Base current		-0.5	A
P <sub>C</sub>	Collector power dissipation	T <sub>C</sub> =25	25	W
T <sub>j</sub>	Junction temperature		150	
T <sub>stg</sub>	Storage temperature		-55~150	

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal resistance from junction to case	5.0	/W

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-50mA, I <sub>B</sub> =0	-50			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =-5mA, I <sub>C</sub> =0	-7			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-2A; I <sub>B</sub> =-0.2A			-1.0	V
V <sub>BE</sub>	Base-emitter on voltage	I <sub>C</sub> =-1A; V <sub>CE</sub> =-4V			-1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-25V; I <sub>E</sub> =0			-100	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-4V; I <sub>C</sub> =0			-100	μA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =-0.1A; V <sub>CE</sub> =-4V	35		320	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =-1A; V <sub>CE</sub> =-4V	35			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-0.5A; V <sub>CE</sub> =-4V	5.0			MHz

◆ h<sub>FE-1</sub> Classifications

A	B	C	D
35-70	60-120	100-200	160-320

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PACKAGE OUTLINE



Fig.2 Outline dimensions(unindicated tolerance:  $\pm 0.10$  mm)